

The drive for excellence

Accelerate your data with the Micron 7600



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Whether powering cloud and data center infrastructures or pushing AI to the edge, the Micron 7600 is the solution to high-throughput, low-latency, power-efficient workloads. Combining an ultra-fast PCIe Gen5 interface with industry-leading G9 NAND technology provides the Micron 7600 the foundation for a broad range of solutions. These solutions include AI inferencing and AI at the edge, where class-leading power efficiency and performance of the Micron 7600 shines.

Key Features

- Power loss protection
- Enterprise data path protection
- NVMe® 2.0b, TCG Opal v2.02, OCP 2.6
- NVMe Management Interface (NVMe-MI™) over SMBus
- NVMe® power states
- Firmware activated without reset
- Secure firmware download
- Hardware root of trust, secure signed firmware
- Self-encrypting drive (SED) with AES-256 encryption
- Micron's Secure Encrypted Environment (SEE)
- Self-monitoring and reporting technology (SMART)
- 5-year limited warranty⁵

Best for



Artificial intelligence



Server memory extension



Massive high-speed OLTP



High-performance computing

Power up your AI inferencing

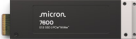
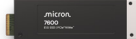
AI inferencing, like all AI workloads, craves high performance memory and storage, but it also requires a balance between that performance and power draw. The Micron® 7600 NVMe™ SSD provides that balance with PCIe Gen5 performance (12GB/s of sequential performance and 2.1 million IOPS of random performance)² and class-leading performance up to 23% higher with 76% better 99th percentile latency¹.

Tame your IO latency

While pure performance makes for great headlines, the true test of your storage subsystem is how well it handles ALL operations — not just the average. The Micron® 7600 NVMe™ SSD delivers class-leading performance up to 23% higher with 76% better 99th percentile latency¹, even the most demanding workloads will have consistent and predictable performance.

Tech-driven storage

The Micron® 7600 NVMe™ SSD is one of the most advanced, highest performing SSDs on the market. Created with Micron-designed controller ASIC, 9th-generation (G9) NAND⁴, and DRAM, this vertically integrated SSD allows for class-leading AI performance and power efficiency. Beyond performance, the Micron 7600 supports new (E1.S, E3.S) and existing (U.2) form factors that dominate the current and emerging storage market.

Micron® 7600 NVMe™ SSD			
			
U.2 15mm	E.3s 7.5mm	E1.S 9.5mm	E1.S 15mm
	7600 PRO 1 DWPD	7600 MAX 3 DWPD	
Capacities ¹	1.92TB-15.36TB	1.6TB-12.8TB	
Sequential reads (MB/s) ²	12,000MB/s	12,000MB/s	
Sequential writes (MB/s) ²	7,000MB/s	7,000MB/s	
Random reads (K IOPS) ²	2,100K	2,100K	
Random writes (K IOPS) ²	400K	700K	
Endurance (DWPD)	1 (random IO)	3 (random IO)	

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1. Micron used the db_bench benchmark for testing RocksDB for random read while writing. SSD comparisons are based on currently in-production and available Gen5 mainstream data center SSDs with read-intensive endurance, from the top five competitive suppliers of OEM data center SSDs by revenue as of February 2025, as per Forward Insights analyst report, "SSD Supplier Status Q4/24". All testing was done by Micron labs.
2. Performance measured under the following conditions: Steady state as defined by SNIA Solid State Storage Performance Test Specification Enterprise v1.1; Drive write cache enabled; NVMe power state 0; Sequential workloads measured using FIO with a queue depth of 32; Random READ workloads measured using FIO with a queue depth of 512; Random WRITE workloads measured using FIO with a queue depth of 128).
3. User capacity: 1GB = 1 billion bytes; formatted capacity is less
4. Refer to <https://www.micron.com/products/storage/nand-flash/g9-nand>
5. Warranty valid for 5 years from the original date of purchase or before writing the maximum total bytes written (TBW) as published in the product datasheet and as measured in the product's SMART data, whichever comes first.